

## N-Channel 200 V (D-S) MOSFET

### PRODUCT SUMMARY

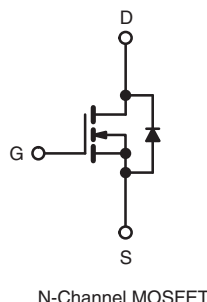
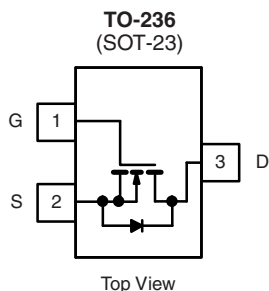
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
200	1.2 at $V_{GS} = 10$ V	0.6

### FEATURES

- DT-Trench Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested

### APPLICATIONS

- Load switch
- Power management for mobile computing


**RoHS**  
 COMPLIANT


### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	0.6	A
		0.5	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	2.5	
Avalanche Current <sup>b</sup>	$I_{AS}$	2.5	mJ
Single Avalanche Energy	$E_{AS}$	53	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	0.6	A
Power Dissipation <sup>a</sup>	$P_D$	1.56	W
		1.19	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	75	100	°C/W
		125	170	
Maximum Junction-to-Foot	$R_{thJF}$	40	55	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

**SPECIFICATIONS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	200			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			75	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 15\text{ V}, V_{GS} = 10\text{ V}$	2.5			A
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}$		1.2	1.4	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 0.5\text{ A}$		4		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}$		3	5	nC
Gate-Source Charge	$Q_{gs}$			0.37		
Gate-Drain Charge	$Q_{gd}$			1.45		
Gate Resistance	$R_g$		0.5	1.3	2.4	$\Omega$
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 33\text{ }\Omega$ $I_D \cong 0.2\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		7	13	ns
Rise Time	$t_r$			10	16	
Turn-Off Delay Time	$t_{d(off)}$			9	15	
Fall Time	$t_f$			11	15	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 0.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}50100$				

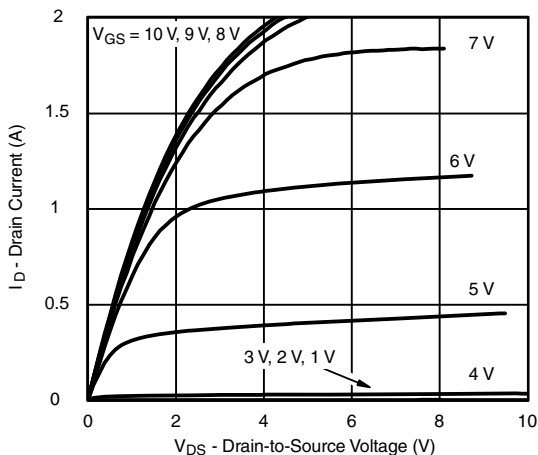
Notes:

a. Pulse test:  $PW \leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

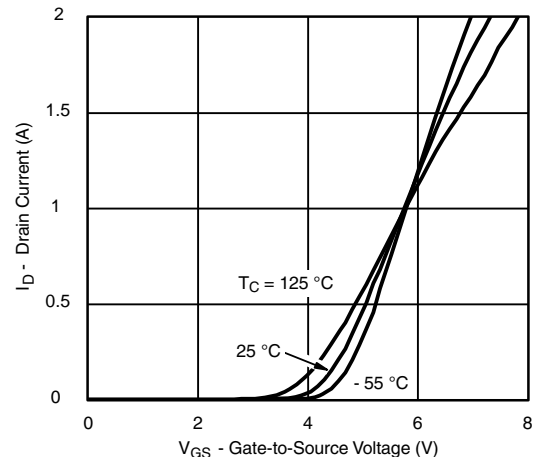
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

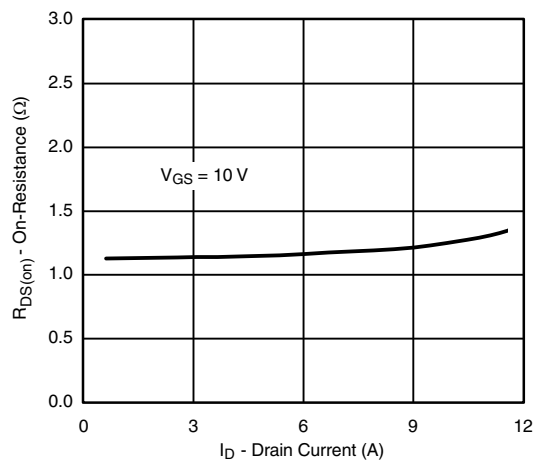


Output Characteristics

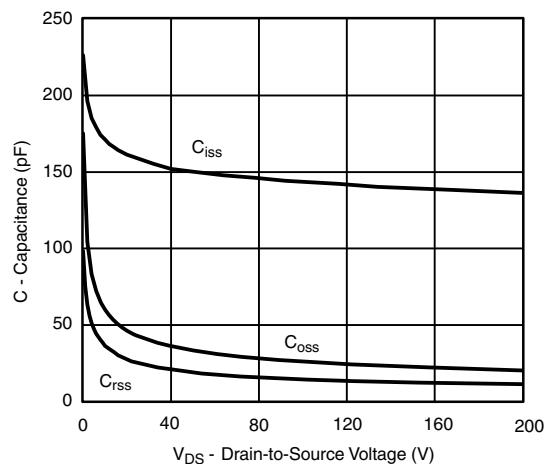


Transfer Characteristics

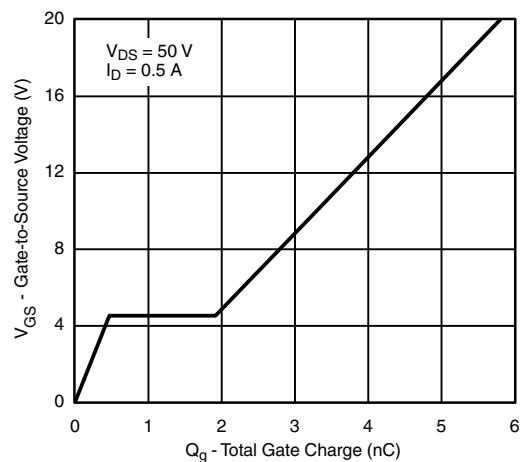
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



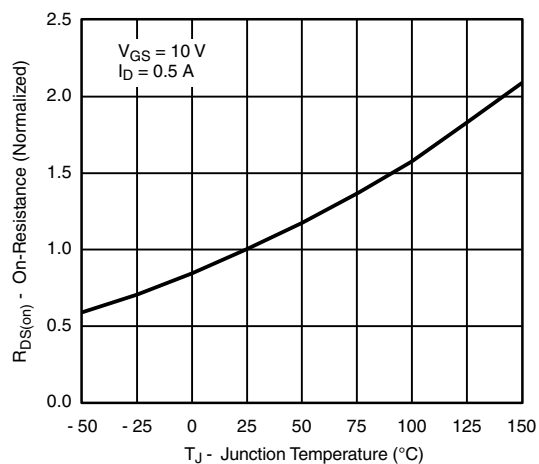
**On-Resistance vs. Drain Current**



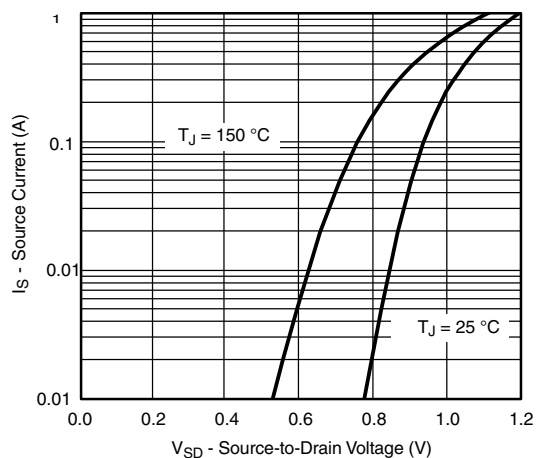
**Capacitance**



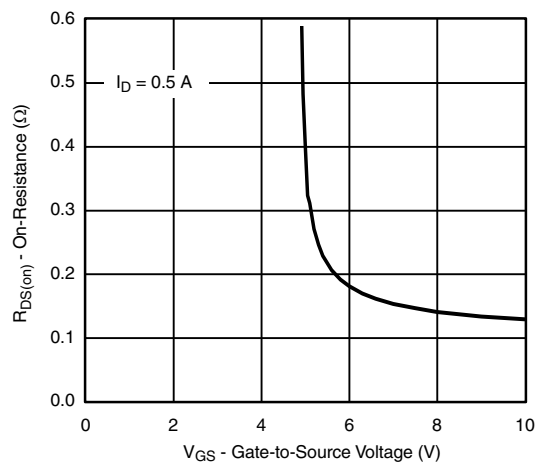
**Gate Charge**



**On-Resistance vs. Junction Temperature**

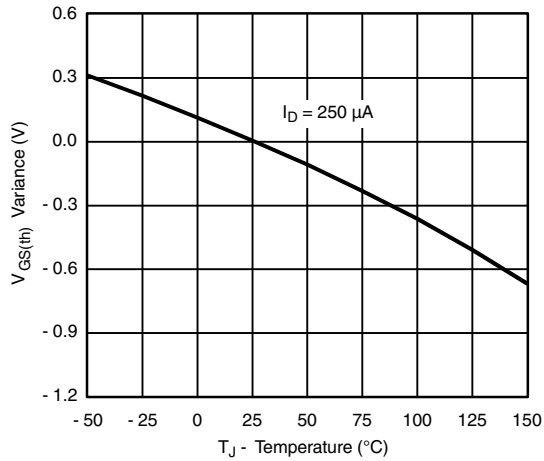


**Source-Drain Diode Forward Voltage**

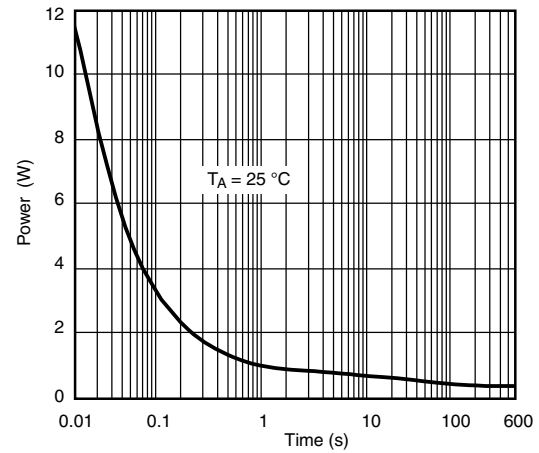


**On-Resistance vs. Gate-to-Source Voltage**

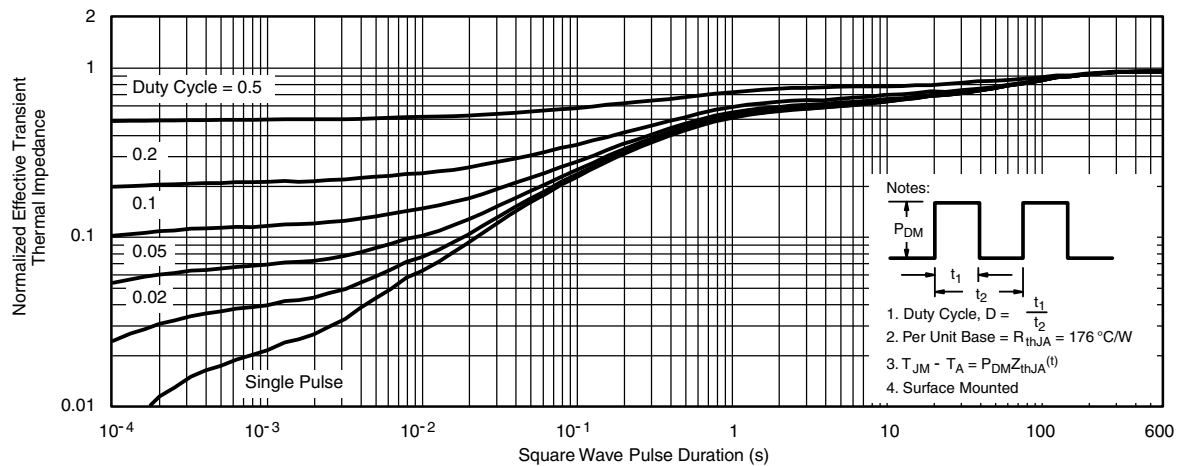
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Threshold Voltage**



**Single Pulse Power**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

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